

March 2015

FGH40N60SFD 600 V, 40 A Field Stop IGBT

Features

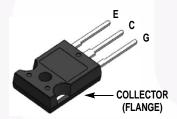
- · High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 2.3 V @ I_C = 40 A
- High Input Impedance
- Fast Switching
- RoHS Compliant

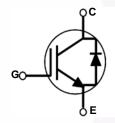
Applications

Solar Inverter, UPS, Welder, PFC, Microwave Oven, Telecom, ESS

General Description

Using novel field stop IGBT technology, Fairchild's field stop IGBTs offer the optimum performance for solar inverter, UPS, welder, microwave oven, telecom, ESS and PFC applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		600	V
V	Gate to Emitter Voltage	±20	V	
V _{GES}	Transient Gate-to-Emitter Voltage	±30	v	
I _C	Collector Current	@ T _C = 25°C	80	А
	Collector Current	$@ T_C = 100^{\circ}C$	40	А
I _{CM (1)}	Pulsed Collector Current @ $T_C = 25^{\circ}C$		120	Α
P _D	Maximum Power Dissipation	@ T _C = 25°C	290	W
	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	116	W
T _J	Operating Junction Temperature	-55 to +150	°C	
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case - 0.43			
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	-	1.45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity	l
FGH40N60SFDTU	FGH40N60SFD	TO-247	Tube	N/A	N/A	30	l

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	600	-	-	V
ΔBV _{CES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	-	0.6	-	V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}$, $V_{GE} = 0 V$	-	-	250	μΑ
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_{C} = 250 \mu\text{A}, V_{CE} = V_{GE}$	4.0	5.0	6.5	V
· GE(III)		I _C = 40 A, V _{GE} = 15 V	_	2.3	2.9	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 40 A, V _{GE} = 15 V, T _C = 125°C	-	2.5	-	V
Dynamic C	haracteristics		1			
C _{ies}	Input Capacitance		-	2110	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	200	-	pF
C _{res}	Reverse Transfer Capacitance	- 1 = 1		60	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	25	-	ns
t _r	Rise Time		- /	42	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	115	-	ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 25^{\circ}C$	-	27	54	ns
E _{on}	Turn-On Switching Loss		-	1.13	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.31	-	mJ
E _{ts}	Total Switching Loss		-	1.44	- /	mJ
t _{d(on)}	Turn-On Delay Time		-	24	-	ns
t _r	Rise Time		-	43	- \	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 40 \text{ A},$	-	120	-	ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	30	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 125°C	-	1.14	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.48	-	mJ
E _{ts}	Total Switching Loss		-	1.62	-	mJ
Q_g	Total Gate Charge		-	120	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 40 \text{ A},$ $V_{GF} = 15 \text{ V}$	-	14	-	nC
Q _{gc}	Gate to Collector Charge	*GE = 10 *	-	58	-	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	$I_F = 20 \text{ A}$	$T_C = 25^{\circ}C$	-	1.95	2.6	V
			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	1.85	-	
t	$\begin{array}{c} \mathbf{t}_{\rm rr} & \text{Diode Reverse Recovery Time} \\ \\ \mathbf{Q}_{\rm rr} & \text{Diode Reverse Recovery Charge} \end{array}$	- I _F =20 A, di _F /dt = 200 A/μs	$T_C = 25^{\circ}C$	-	45	-	ns
11			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	140	ı	
Qrr			$T_{\rm C} = 25^{\rm o}{\rm C}$	ı	75	i	nC
~II			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	375	ı	:

Figure 1. Typical Output Characteristics

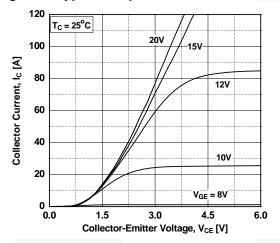


Figure 3. Typical Saturation Voltage Characteristics

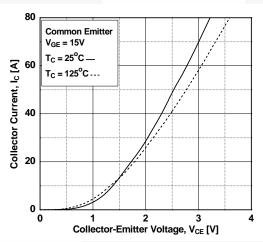


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

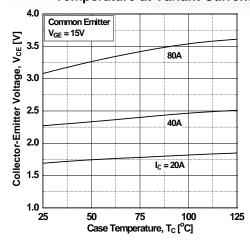


Figure 2. Typical Output Characteristics

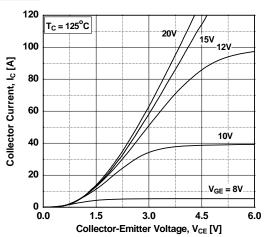


Figure 4. Transfer Characteristics

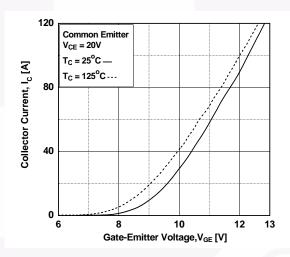


Figure 6. Saturation Voltage vs. V_{GE}

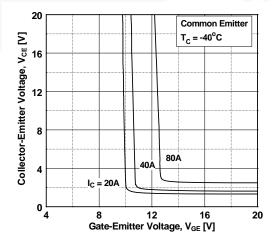


Figure 7. Saturation Voltage vs. V_{GE}

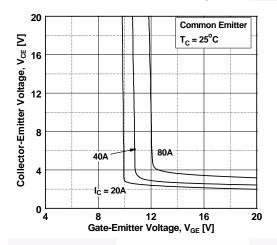


Figure 9. Capacitance Characteristics

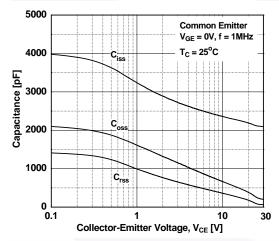


Figure 11. SOA Characteristics

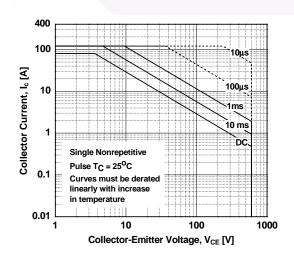


Figure 8. Saturation Voltage vs. V_{GE}

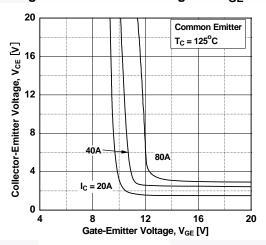


Figure 10. Gate charge Characteristics

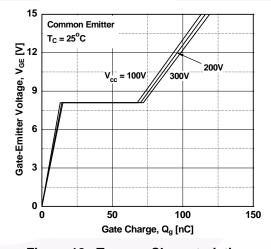


Figure 12. Turn-on Characteristics vs. Gate Resistance

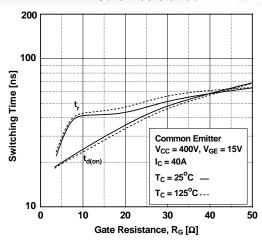


Figure 13. Turn-off Characteristics vs.
Gate Resistance

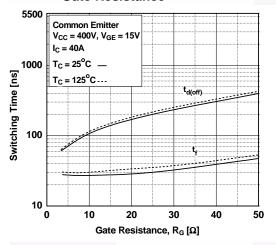


Figure 15. Turn-off Characteristics vs. Collector Current

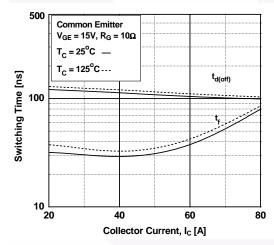


Figure 17. Switching Loss vs. Collector Current

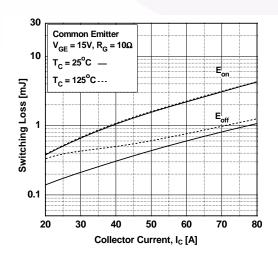


Figure 14. Turn-on Characteristics vs.
Collector Current

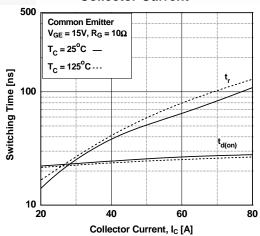


Figure 16. Switching Loss vs. Gate Resistance

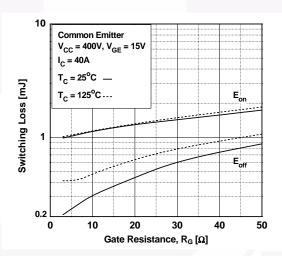


Figure 18. Turn off Switching SOA Characteristics

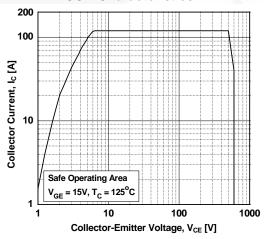


Figure 19. Forward Characteristics

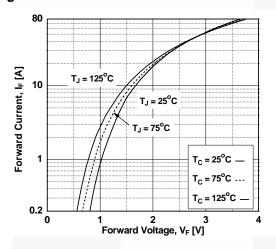


Figure 20. Reverse Current

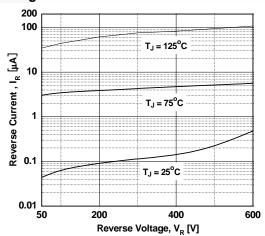


Figure 21. Stored Charge

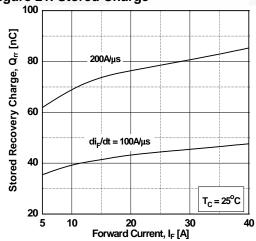


Figure 22. Reverse Recovery Time

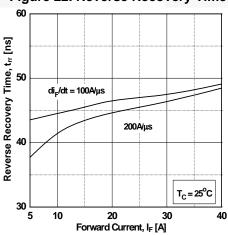
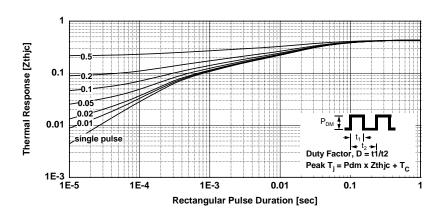
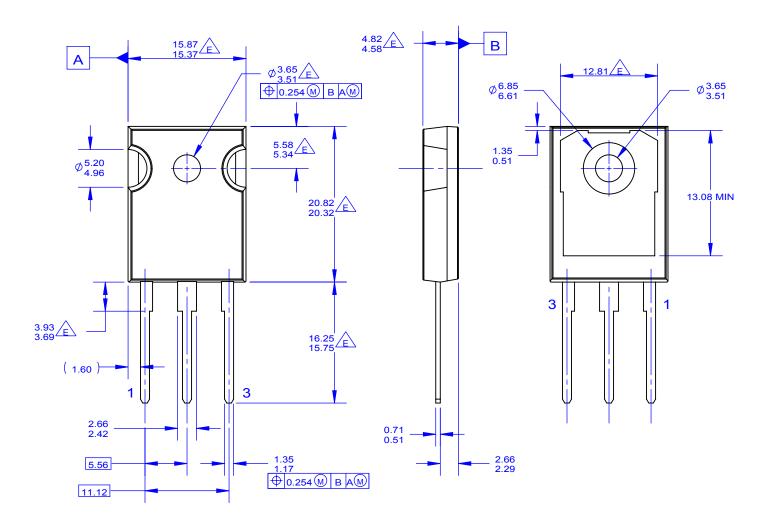


Figure 23. Transient Thermal Impedance of IGBT





NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004. B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
- FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994

DOES NOT COMPLY JEDEC STANDARD VALUE F. DRAWING FILENAME: MKT-TO247A03_REV03





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

 $\begin{array}{lll} \mathsf{AccuPower^{\mathsf{TM}}} & \mathsf{F-PFS^{\mathsf{TM}}} \\ \mathsf{AttitudeEngine^{\mathsf{TM}}} & \mathsf{FRFET}^{\texttt{®}} \end{array}$

Awinda[®] Global Power Resource SM

AX-CAP®* GreenBridge™
BitSiC™ Green FPS™
Build it Now™ Green FPS™ e-Series™

Current Transfer Logic™ Making Small Speakers Sound Louder

DEUXPEED® and Better™

Dual Cool™ MegaBuck™

EcoSPARK® MICROCOUPLER™

EfficientMax™ MicroFET™

EfficientMax™ MicroFET™
ESBC™ MicroPak™
MicroPak™
MicroPak2™
Fairchild® MillerDrive™
MotionMax™
Fairchild Semiconductor®

Farchild Semiconductor

FACT Quiet Series™
FACT®

FastvCore™
FETBench™
FPS™

MotionGrid®
MTI®
MTX®
MVN®
FETBench™
MVN®
FPS™

OptoHiT™
OPTOLOGIC®

OPTOPLANAR®

Power Supply WebDesigner™ PowerTrench®

PowerXS™

Programmable Active Droop™ OFFT®

QS™ Quiet Series™ RapidConfigure™

T TM

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™

SYSTEM GENERAL®'
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyPWM™
TranSiC™
TriFault Detect™
TRUECURRENT®**
uSerDes™

SerDes"
UHC[®]
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
XS™
XS™

仙童®

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT http://www.fairchildsemi.com, FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Definition of Terms						
Datasheet Identification	Product Status	Definition				
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.				
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.				
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.				
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.				

Rev. 177

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor:

FGH40N60SFDTU FGH40N60SFDTU_F085